c) Amendments to the Claims

Please cancel claims 1-32 without prejudice or disclaimer of subject matter presented herein. Please add new Claims 33-40 as follows.

Claims 1-32 (canceled).

Claim 33 (new): A deposited film-forming process for forming under vacuum a deposited film on a substrate arranged in a reaction chamber and having a glow discharge region by introducing a raw material gas into said reaction chamber and introducing a high frequency power into said reaction chamber to cause glow discharge in said glow discharge region of said reaction chamber thereby forming said deposited film on said substrate, comprising:

introducing said high frequency power into said reaction chamber employing a high frequency power introduction means having an electrode for transmitting said high frequency power; and providing a region where impedance is discontinuous by employing the electrode which comprises electrically conductive metallic material and being patterned in a configuration which is branched into plural portions such that the region where impedance is discontinuous is provided so as to generate a uniform supply of said high frequency power to said reaction chamber, said high frequency power introduction means has (i) a first insulating surface in contact with said electrode such that there is no clearance between said electrically conductive metallic material constituting said electrode and said first insulating surface and (ii) a second insulating surface for

insulating said electrically conductive metallic material constituting said electrode from said glow discharge region of said reaction chamber.

Claim 34 (new): The deposited film-forming process according to claim 33, wherein said high frequency power is of an oscillation frequency in a range of from 20 MHz to 450 MHz.

Claim 35 (new): The deposited film-forming process according to claim 33, wherein said high frequency power introduction means is cooled.

Claim 36 (new): The deposited film-forming process according to claim 33, wherein said high frequency power introduction means is heated.

Claim 37 (new): The deposited film-forming process according to claim 33, wherein said substrate arranged in said reaction chamber comprises a plurality of cylindrical substrates and said plurality of cylindrical substrates are spacedly and concentrically arranged so as to circumscribe said glow discharge region.

Claim 38 (new) The deposited film-forming process according to claim 33, wherein said first insulating surface (i) and said second insulating surface (ii) comprise a ceramic material.

Claim 39 (new): The deposited film-forming process according to claim 38, wherein said ceramic material is an alumina ceramic material.

Claim 40 (new): The deposited film-forming process according to claim 33, wherein a portion of said second insulating surface (ii) is exposed to said glow discharge caused in said glow discharge region of said reaction chamber and said portion has a surface roughness of 5 to 200 μm in terms of JIS ten-point average roughness (RZ) under JIS B0601.